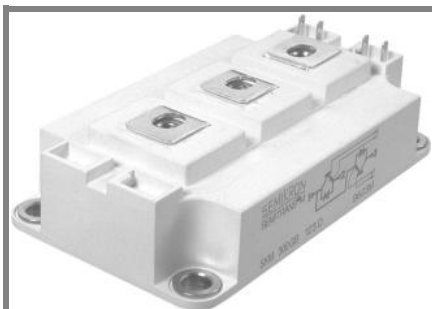




SEMITRANS® 3

Trench IGBT Modules

SKM 600GB066D

Features

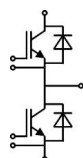
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Remarks

- Case temp. limited. to $T = 125^\circ\text{C}$, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_{j \leq 150^\circ\text{C}}$
- SC data: $t_p \leq 6\mu\text{s}$; $V_{GE} \leq 15\text{V}$; $T_j = 150^\circ\text{C}$; $V_{CC} \leq 360\text{V}$, use of soft R_G necessary !
- Take care of over-voltage caused by stray induct.
- $I_{DC} \leq 500\text{A}$ for $T_{Terminal} = 100^\circ\text{C}$

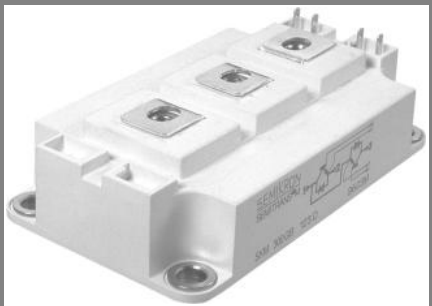


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Absolute Maximum Ratings		T _{case} = 25°C, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT				
V _{CES}	T _j = 25 °C	600	V	
I _C	T _j = 175 °C	T _c = 25 °C	760	A
		T _c = 80 °C	570	A
I _{CRM}	I _{CRM} =1,33xI _{Cnom}	800	A	
V _{GES}		±20	V	
t _{psc}	V _{CC} = 360 V; V _{GE} ≤ 15 V; T _j = 150 °C V _{CES} < 600 V	6	μs	
Inverse Diode				
I _F	T _j = 175 °C	T _c = 25 °C	700	A
		T _c = 80 °C	510	A
I _{FRM}	I _{FRM} =1,33xI _{Fnom}	800	A	
Module				
I _{t(RMS)}		500	A	
T _{vj}		- 40 + 175	°C	
T _{stg}		- 40 + 125	°C	
V _{isol}	AC, 1 min.	4000	V	

Characteristics			T _{case} = 25°C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 9,6 mA		5	5,8	6,5	V	
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C			0,3	0,9	mA	
V _{CE0}				T _j = 25 °C	0,9	1	V
				T _j = 150 °C	0,85	0,9	V
r _{CE}	V _{GE} = 15 V			T _j = 25°C	0,9	1,5	mΩ
				T _j = 150°C	1,4	2	mΩ
V _{CE(sat)}	I _{Cnom} = 600 A, V _{GE} = 15 V			T _j = 25°C _{chiplev.}	1,45	1,9	V
				T _j = 150°C _{chiplev.}	1,7	2,1	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz				37		nF
C _{oes}					2,3		nF
C _{res}					1,1		nF
Q _G	V _{GE} = -8V...+15V				4400		nC
R _{Gint}	T _j = °C				0,5		Ω
t _{d(on)}	R _{Gon} = 1,5 Ω		V _{CC} = 300V I _C = 600A	270			ns
t _r				77			ns
E _{on}				7,5			mJ
t _{d(off)}	R _{Goff} = 1,5 Ω		T _j = 150 °C V _{GE} = -8V/+15V	670			ns
t _f				77			ns
E _{off}				29,5			mJ
R _{th(j-c)}	per IGBT				0,08		K/W

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SEMITRANS® 3

Trench IGBT Modules

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Features

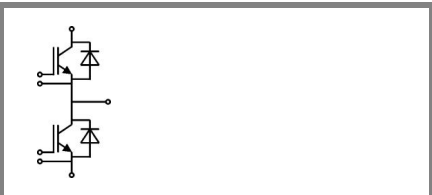
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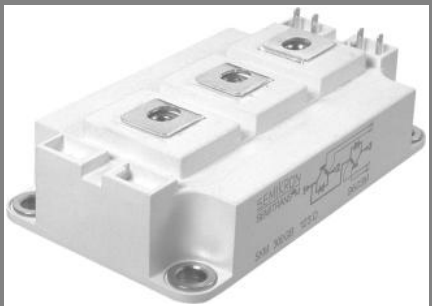
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 600 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,4	1,6	V
V _{F0}		T _j = 25 °C		0,95	1	V
r _F		T _j = 25 °C		0,8	1	mΩ
I _{RRM}	I _F = 600 A	T _j = 150 °C		580		A
Q _{rr}	di/dt = 8600 A/μs			105		μC
E _{rr}	V _{GE} = -8 V; V _{CC} = 300 V			25		mJ
R _{th(j-c)D}	per diode				0,125	K/W
Module						
L _{CE}				15	20	nH
R _{CC'+EE'}	res., terminal-chip	T _{case} = 25 °C		0,35		mΩ
		T _{case} = 125 °C		0,5		mΩ
R _{th(c-s)}	per module				0,038	K/W
M _s	to heat sink M6		3		5	Nm
M _t	to terminals M6		2,5		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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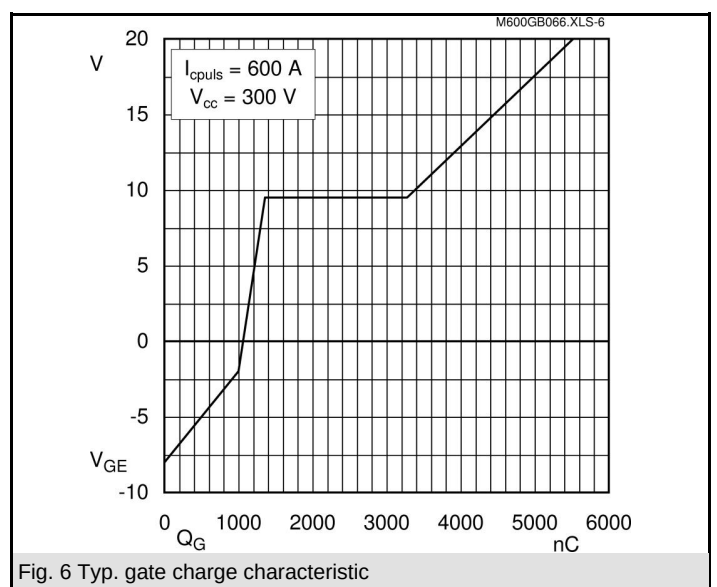
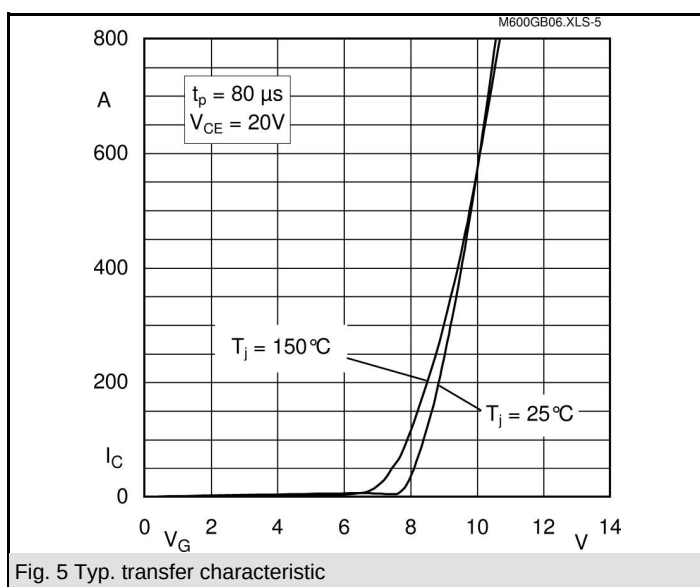
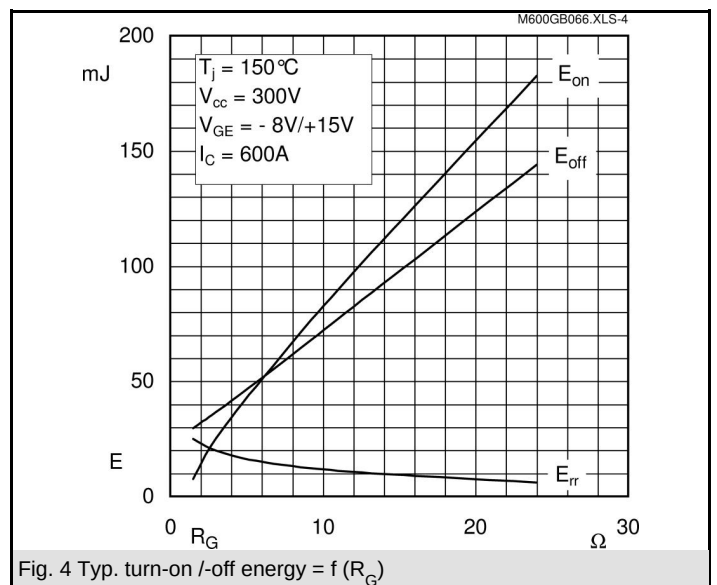
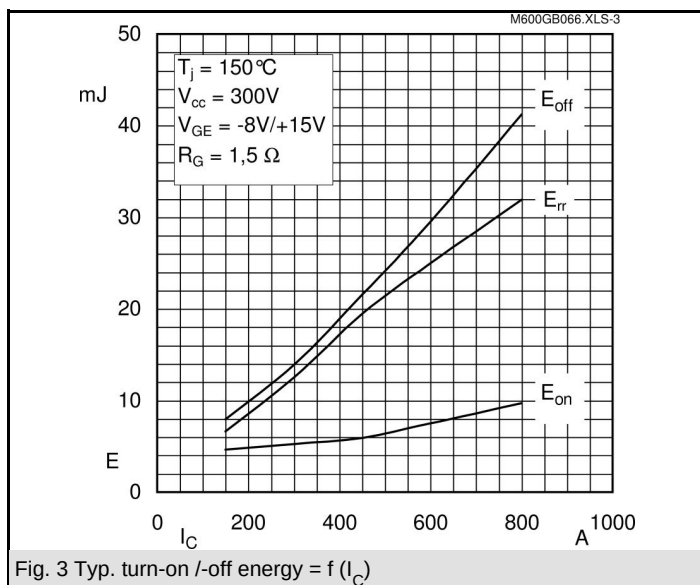
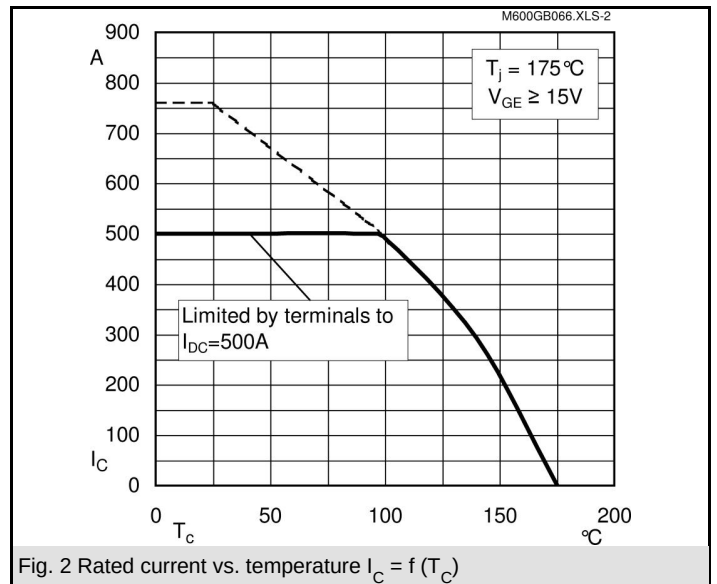
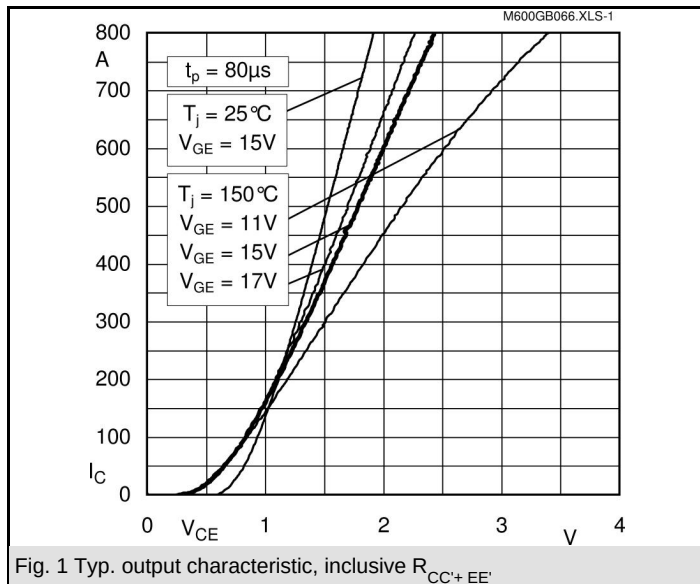
Remarks

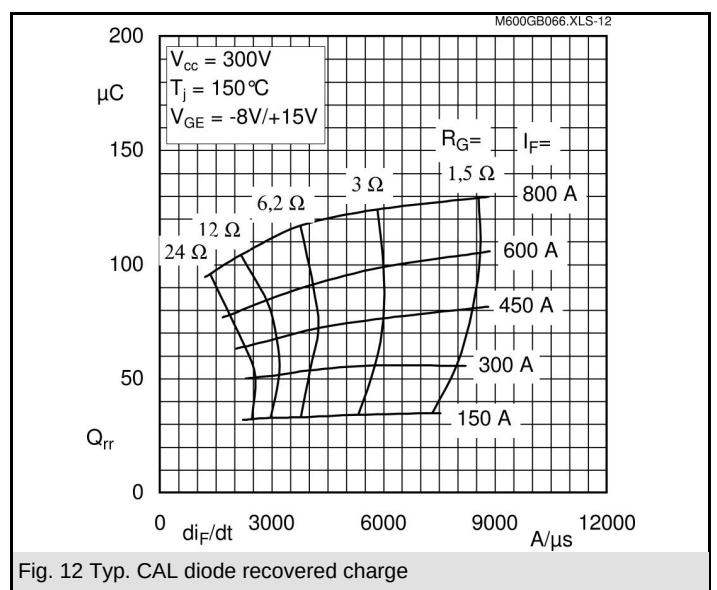
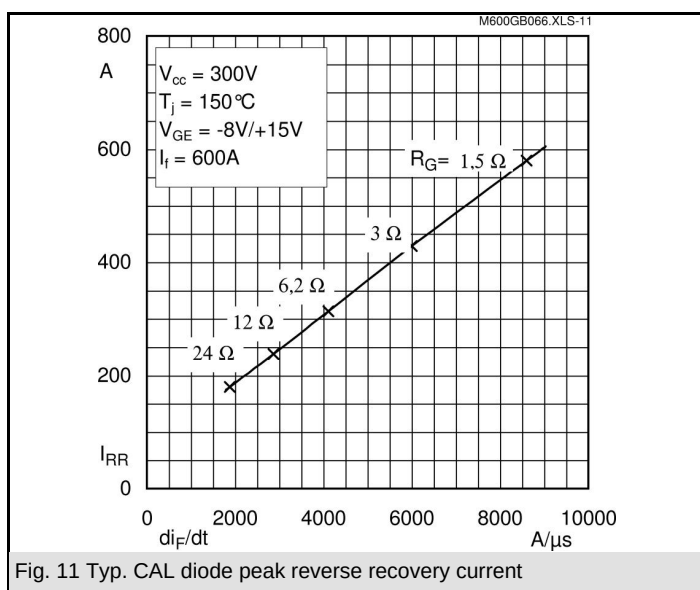
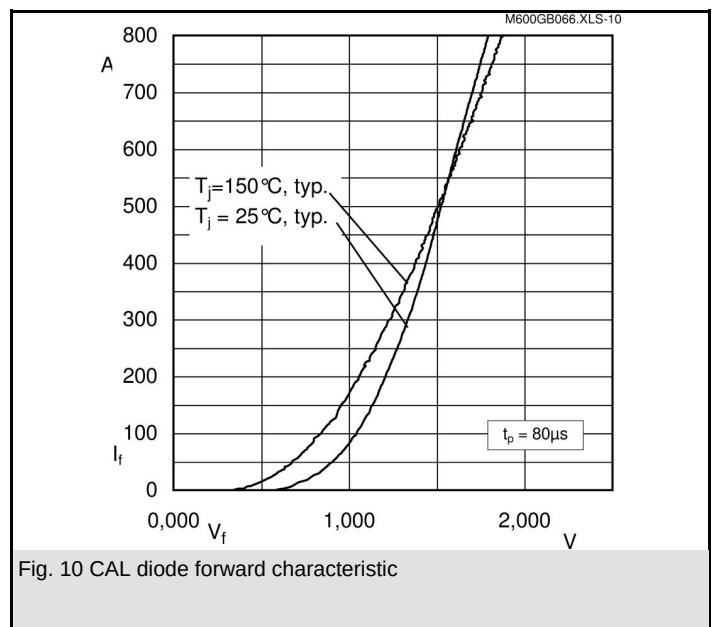
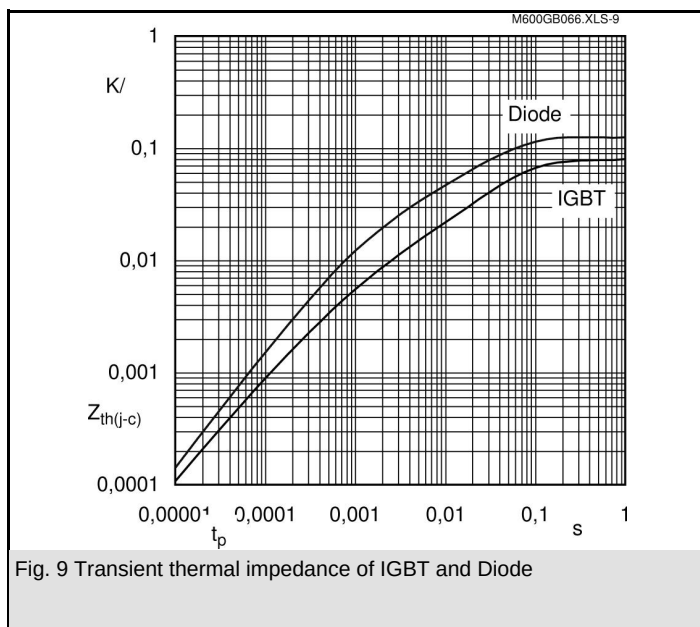
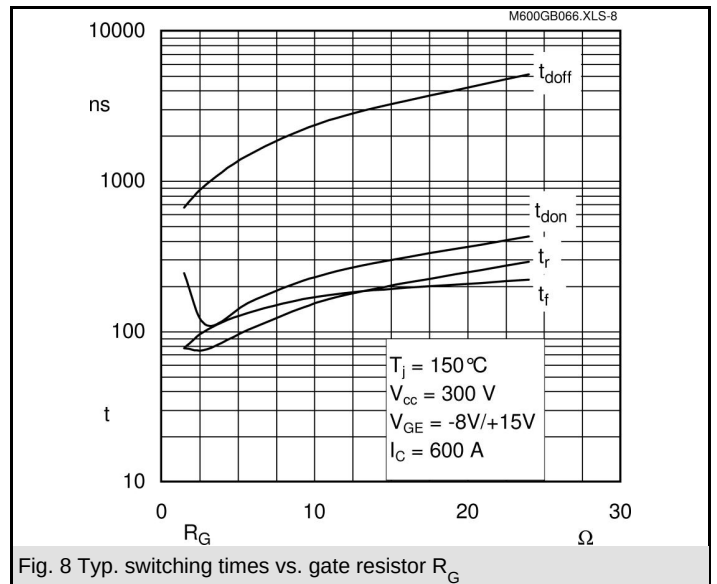
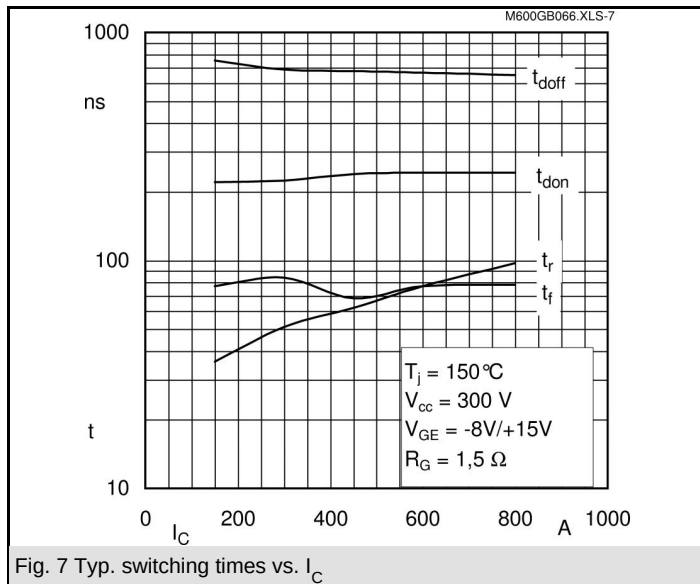
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Z_{th}			
Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	$i = 1$	48,4	mk/W
R_i	$i = 2$	19,5	mk/W
R_i	$i = 3$	3,1	mk/W
R_i	$i = 4$	4	mk/W
τ_{u_i}	$i = 1$	0,054	s
τ_{u_i}	$i = 2$	0,0144	s
τ_{u_i}	$i = 3$	0,0012	s
τ_{u_i}	$i = 4$	0,0026	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	80	mk/W
R_i	$i = 2$	33	mk/W
R_i	$i = 3$	10,5	mk/W
R_i	$i = 4$	1,5	mk/W
τ_{u_i}	$i = 1$	0,054	s
τ_{u_i}	$i = 2$	0,01	s
τ_{u_i}	$i = 3$	0,0007	s
τ_{u_i}	$i = 4$	0,0019	s



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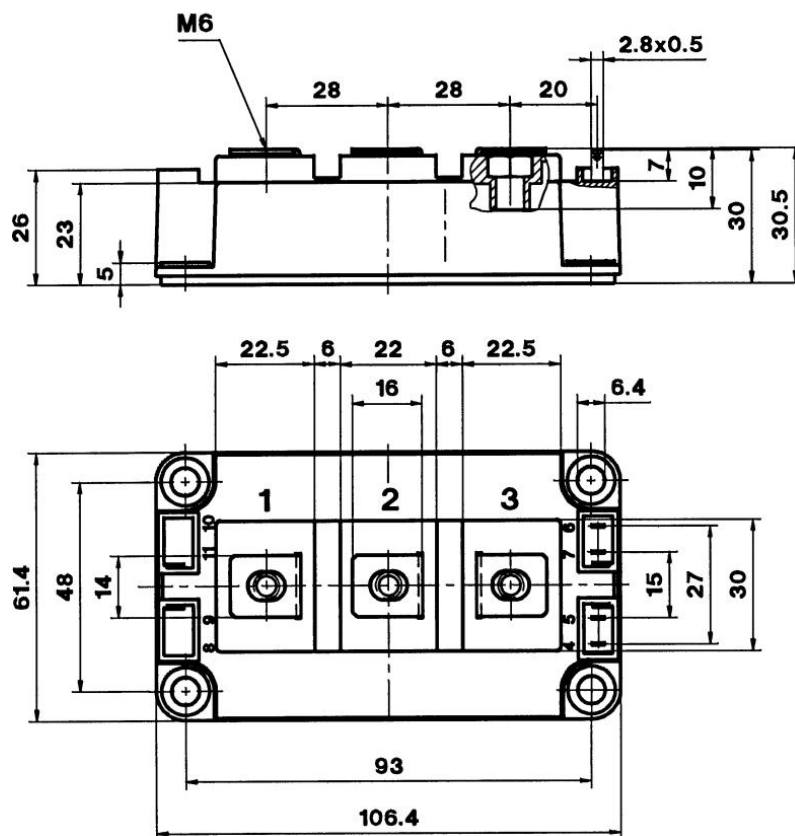




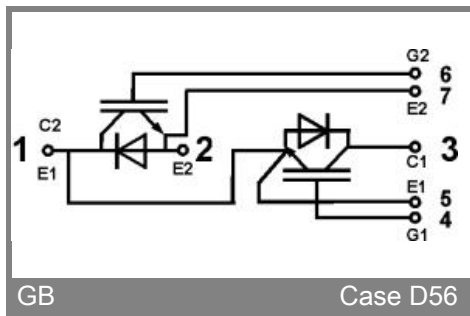
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